查询2SC5070供应商

NPN Epitaxial Planar Silicon Transistor

2SC5070

Low-Frequency General-Purpose Amplifier, Driver Applications

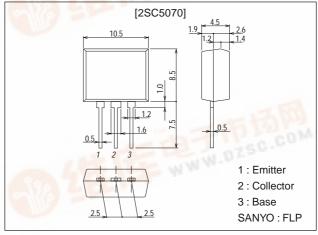
Features

- · High current capacity.
- · Adoption of MBIT process.
- · High DC current gain.
- · Low collector-to-emitter saturation voltage.
- \cdot High V_{EBO}.

Package Dimensions

unit:mm





Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		30	V
Collector-to-Emitter Voltage	VCEO		25	V
Emitter-to-Base Voltage	VEBO	14	15	V
Collector Current	IC	- FP	2	A
Collector Current (Pulse)	ICP	1 Mar 1997 1997	4	А
Base Current	۱ _B		0.4	A
Collector Dissipation	PC		1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	224	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0			100	nA
Emitter Cutoff Current	IEBO	V _{EB} =10V, I _C =0		1.20	100	nA
DC Current Gain	h _{FE} 1	V _{CE} =5V, I _C =500mA	800	1500	3200	10
	h _{FE} 2	V _{CE} =5V, I _C =1A	600	40.16		
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =50mA	10.00	260		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		27		pF

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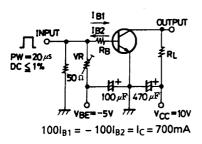
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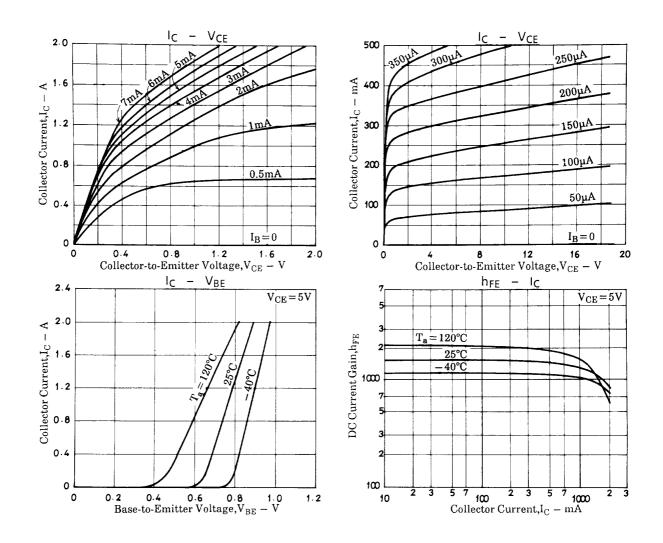
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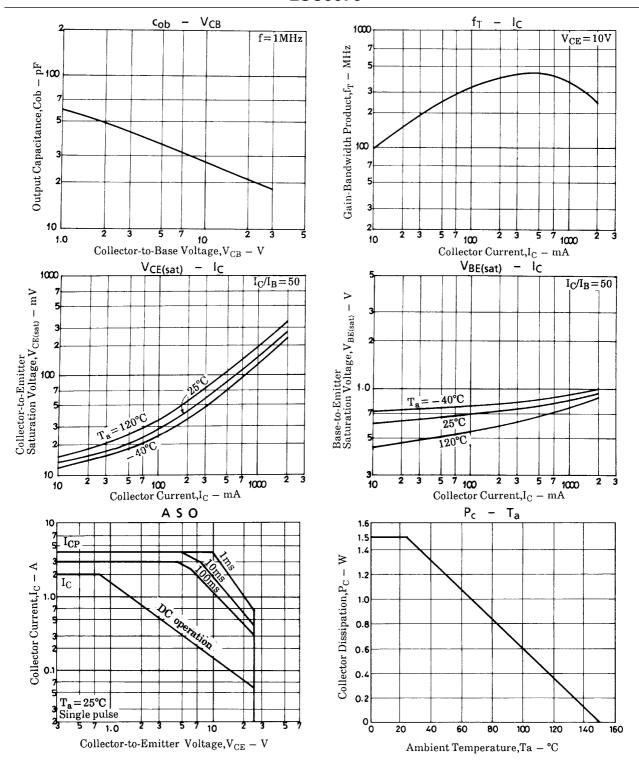
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A, I _B =20mA		0.15	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1A, I _B =20mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =10μA, I _E =0	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	25			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0	15			V
Turn-ON Time	ton	See specified Test Circuit		0.14		μs
Strage Time	tstg	See specified Test Circuit		1.35		μs
Fall Time	tf	See specified Test Circuit		0.1		μs

Switching Time Test Circuit





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